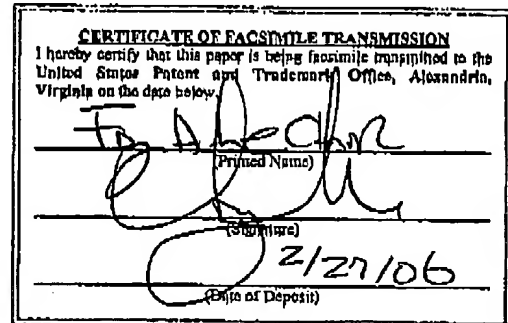


FEB 27 2006

Atty. Dkt. No. 039153-0649 (H0982)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Xiang et al.
Title: FULLY DEPLETED STRAINED
SILICON ON INSULATOR
TRANSISTOR AND METHOD
OF MAKING THE SAME
Appl. No.: 10/773,026
Filing Date: 02/05/2004
Examiner: Doty, Heather Anne
Art Unit: 2813



AMENDMENT AND REPLY UNDER 37 CFR 1.111

Mail Stop AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This communication is responsive to the Non-Final Office Action dated November 30, 2005, concerning the above-referenced patent application.

Amendment to the Title begin on page 3 of this document.

Amendments to the Abstract are presented as a new Abstract attached to this document for insertion after the claim pages of the application (or to replace the previously submitted Abstract).

Amendments to the Claims are reflected in the listing of claims which begins on page 4 of this document.

Atty. Dkt. No. 039153-0649 (H0982)

Remarks/Arguments begin on page 8 of this document.

Please amend the application as follows:

Atty. Dkt. No. 039153-0649 (H0982)

Amendments to the Title:

Please amend the Title as follows:

**FULLY DEPLETED STRAINED ~~SILICON~~ SEMICONDUCTOR ON INSULATOR
TRANSISTOR AND METHOD OF MAKING THE SAME**